



FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

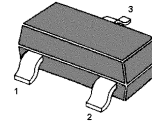
TEL: 852-2790 0314 FAX: 852-2790 0206

MMBTSA1162

PNP Silicon Epitaxial Planar Transistor

for AF general purpose amplifier applications.

The transistor is subdivided into three groups O, Y and G, according to its DC current gain. As complementary type the NPN transistor MMBTSC2712 is recommended.

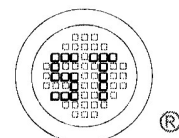


1. Base 2. Emitter 3. Collector

SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	150	mA
Base Current	$-I_B$	30	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_S	-55 to 125	$^\circ\text{C}$



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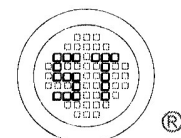
Dated : 20/10/2005

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MMBTSA1162**Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$**

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}=6\text{V}$, $-I_C=2\text{mA}$					
Current Gain Group O	h_{FE}	70	-	140	-
Y	h_{FE}	120	-	240	-
G	h_{FE}	200	-	400	-
Collector Base Breakdown Voltage at $-I_C=100\mu\text{A}$	$-V_{(BR)CBO}$	50	-	-	V
Collector Emitter Breakdown Voltage at $-I_C=10\text{mA}$	$-V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $-I_E=10\mu\text{A}$	$-V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current at $-V_{CB}=50\text{V}$	$-I_{CBO}$	-	-	0.1	μA
Emitter Cutoff Current at $-V_{EB}=5\text{V}$	$-I_{EBO}$	-	-	0.1	μA
Collector Saturation Voltage at $-I_C=100\text{mA}$, $-I_B=10\text{mA}$	$-V_{CE(sat)}$	-	-	0.3	V
Gain Bandwidth Product at $-V_{CE}=10\text{V}$, $-I_C=1\text{mA}$	f_T	80	-	-	MHz
Output Capacitance at $-V_{CB}=10\text{V}$, $f=1\text{MHz}$	C_{OB}	-	-	7	pF
Noise Figure at $-V_{CE}=6\text{V}$, $-I_C=0.1\text{mA}$, $f=100\text{Hz}$, $R_S=10\text{K}\Omega$	NF	-	0.5	6	dB

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